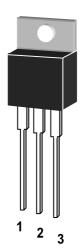
MJE13006 / MJE13007

NPN Silicon Power Transistors

High Voltage Switch Mode Application

High Speed Switching

Suitable for Switching Regulator and Motor Control



1. Base 2. Collector 3. Emitter

TO-220 Plastic Package

Absolute Maximum Ratings (T_a=25°C)

		Symbol	Value	Unit
Collector Base Voltage	MJE13006	V _{CBO}	600	V
	MJE13007		700	V
Collector Emitter Voltage	MJE13006	V _{CEO}	300	V
	MJE13007		400	V
Emitter Base Voltage		V _{EBO}	9	V
Collector Current (DC)		I _C	8	Α
Collector Current (Pulse)		I _{CP}	16	Α
Base Current		I _B	4	Α
Power Dissipation		P _{tot}	80	W
Junction Temperature		T _J	150	°С
Storage Temperature Range		T _S	-65 to +150	οС

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.







Dated: 07/12/2002

MJE13006 / MJE13007

Characteristics at Ta=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =5V, I _C =2A		h_FE	8	-	60	-
at V_{CE} =5 V , I_{C} =5 A		h_{FE}	5	-	30	-
Collector Emitter Breakdown Voltage						
at I _C =10mA	MJE13006	BV_CEO	300	-	-	V
	MJE13007	BV_CEO	400	-	-	V
Emitter Cutoff Current						
at V _{EB} =9V		I _{EBO}	-	-	1	mA
Collector Emitter Saturation Voltage						
at $I_C=2A$, $I_B=0.4A$		$V_{CE(sat)}$	-	-	1	V
at I _C =5A, I _B =1A		$V_{CE(sat)}$	-	-	2	V
at I _C =8A, I _B =2A		$V_{CE(sat)}$	-	-	3	V
Base Emitter Saturation Voltage						
at $I_C=2A$, $I_B=0.4A$		$V_{BE(sat)}$	-	-	1.2	V
at I _C =5A, I _B =1A		$V_{BE(sat)}$	-	-	1.6	V
Current Gain Bandwidth Product						
at V_{CE} =10V, I_{C} =0.5A		f_T	4	-	-	MHz
Output Capacitance						
at V _{CB} =10V, f=0.1MHz		C_{ob}		110		pF
Turn ON Time	V _{CC} =125V,I _C =5A,	t _{ON}	-	-	1.6	μS
Storage Time	I _{B1} =-I _{B2} =1A,	t _S	-	-	3	μS
Fall Time	R_L =50 Ω	t _F	-	-	0.7	μS

Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.

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